

FEATURES

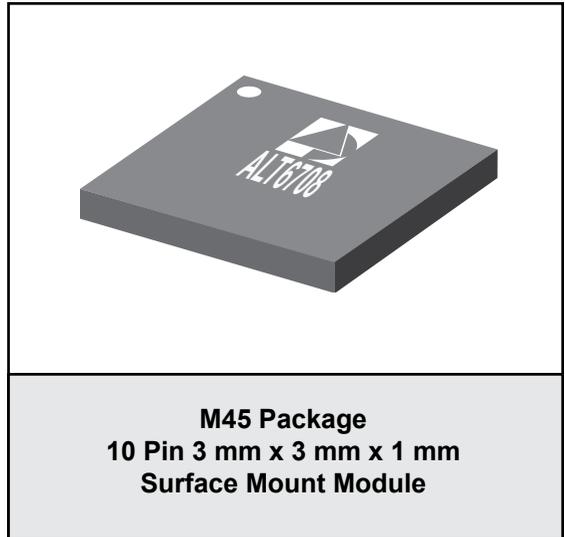
- HSPA, LTE Compliant
- 4th Generation HELP™ technology
- High Efficiency (R99 waveform):
 - 40 % @ P_{OUT} = +28.8 dBm
 - 26 % @ P_{OUT} = +17 dBm
 - 17 % @ P_{OUT} = +13.5 dBm
 - 18 % @ P_{OUT} = +7.5 dBm
 - 10 % @ P_{OUT} = +3.5 dBm
- Low Quiescent Current: 3 mA
- Low Leakage Current in Shutdown Mode: <5 μA
- Internal Voltage Regulator
- Integrated “daisy chainable” directional coupler with CPL_{IN} and CPL_{OUT} port.
- Internal DC Blocks on all RF ports
- Optimized for a 50 Ω System
- 1.8V Control Logic
- RoHS Compliant Package, 260 °C MSL-3

APPLICATIONS

- Band 8 LTE Wireless Devices
- Band 8 (EGSM) WCDMA/HSPA Wireless Devices

PRODUCT DESCRIPTION

The ALT6708 HELP4™ PA is a 4th generation HELP™ product for LTE and WCDMA devices operating in UMTS900 (Band 8) . This PA incorporates ANADIGICS’ HELP4™ technology to deliver exceptional efficiency at low power levels and low quiescent current without the need for external voltage regulators or converters. The device is manufactured using advanced InGaP-Plus™ HBT technology offering state-of-the-art reliability, temperature stability, and ruggedness. Three selectable bias modes that optimize efficiency for different output power levels and a shutdown mode with low leakage current increase handset talk and standby time. A “daisy chainable” directional coupler is



integrated in the module, thus eliminating the need of an external coupler. The self-contained 3 mm x 3 mm x 1 mm surface mount package incorporates matching networks optimized for output power, efficiency, and linearity in a 50 Ω system.

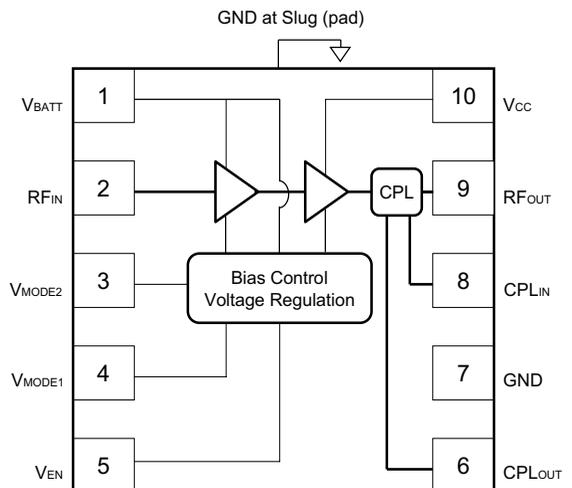


Figure 1: Block Diagram

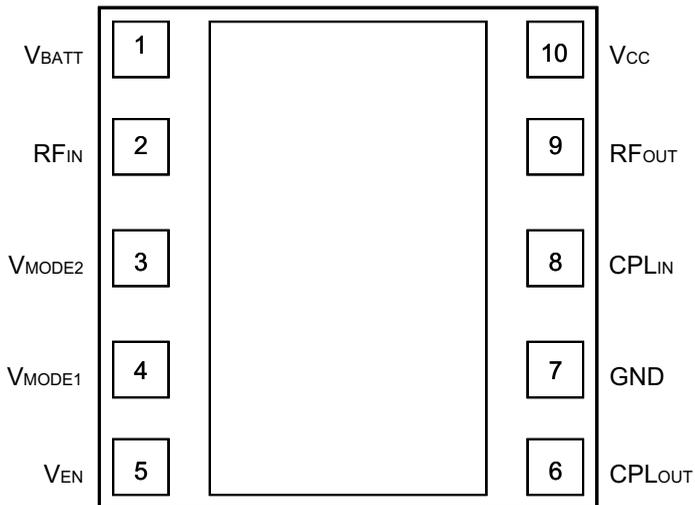


Figure 2: Pinout (X-ray Top View)

Table 1: Pin Description

| PIN | NAME | DESCRIPTION |
|-----|--------|------------------------|
| 1 | VBATT | Battery Voltage |
| 2 | RFIN | RF Input |
| 3 | VMODE2 | Mode Control Voltage 2 |
| 4 | VMODE1 | Mode Control Voltage 1 |
| 5 | VEN | PA Enable Voltage |
| 6 | CPLOUT | Coupler Output |
| 7 | GND | Ground |
| 8 | CPLIN | Coupler Input |
| 9 | RFOUT | RF Output |
| 10 | VCC | Supply Voltage |

ELECTRICAL CHARACTERISTICS

Table 2: Absolute Minimum and Maximum Ratings

| PARAMETER | MIN | MAX | UNIT |
|---|-----|------|------|
| Supply Voltage (V_{CC}) | 0 | +5 | V |
| Battery Voltage (V_{BATT}) | 0 | +6 | V |
| Control Voltages (V_{MODE1} , V_{MODE2} , V_{EN}) | 0 | +3.5 | V |
| RF Input Power (P_{IN}) | - | +10 | dBm |
| Storage Temperature (T_{STG}) | -40 | +150 | °C |

Stresses in excess of the absolute ratings may cause permanent damage. Functional operation is not implied under these conditions. Exposure to absolute ratings for extended periods of time may adversely affect reliability.

Table 3: Operating Ranges

| PARAMETER | MIN | TYP | MAX | UNIT | COMMENTS |
|--|------------|-----------|--------------|------|---|
| Operating Frequency (f) | 880 | - | 915 | MHz | |
| Supply Voltage (V_{CC}) | +3.1 | +3.4 | +4.35 | V | $P_{OUT} < +28.8$ dBm |
| Enable Voltage (V_{EN}) | +1.35 0 | +1.8 - | +3.1 +0.5 | V | PA "on" PA "shut down" |
| Mode Control Voltage (V_{MODE1} , V_{MODE2}) | +1.35 0 | +1.8 - | +3.1 +0.5 | V | Low Bias Mode High Bias Mode |
| WCDMA/UMTS Output Power ^(1, 3) | | | | | |
| R99 WCDMA, HPM | 28.0 | 28.8 | - | dBm | 3GPP TS 34.121-1, Rel 8 Table C.11.1.3, SUBTEST 1 |
| HSPA (MPR=0), HPM | 26.9 | 27.7 | - | | |
| LTE ⁽²⁾ | 26.9 | 27.7 | - | | |
| R99 WCDMA, MPM | - | 17.0 | - | | |
| LTE ⁽²⁾ & HSPA (MPR=0), MPM | - | 16.0 | - | | |
| R99 WCDMA, LPM | - | 7.5 | - | | |
| LTE ⁽²⁾ & HSPA (MPR=0), LPM | | 6.5 | | | TS 36.101 Rel 8 for LTE |
| Case Temperature (T_C) | -40 | - | +90 | °C | |

The device may be operated safely over these conditions; however, parametric performance is guaranteed only over the conditions defined in the electrical specifications.

Notes:

- (1) For operation at 3.1 V, P_{OUT} is derated by 0.8 dB.
- (2) LTE waveform characteristics: up to 15MHz, QPSK, RB = 16.
- (3) For Operation at +105 °C, P_{OUT} is derated by 1.0 dB.

Table 4: Electrical Specifications - LTE Operation (RB = 12, START = 0, QPSK)
(T_c = +25 °C, V_{BATT} = V_{CC} = +3.4 V, V_{EN} = +1.8 V, 50 Ω system)

| PARAMETER | MIN | TYP | MAX | UNIT | COMMENTS | | |
|--|----------------|----------------------|-------------------|--------|--|-----------------------|---------------------|
| | | | | | P _{OUT} | V _{MODE1} | V _{MODE2} |
| Gain | 25 14 9 | 27.5 17.5 12.5 | 31 21 16 | dB | P _{OUT} = +27.7 dBm P _{OUT} = +16 dBm P _{OUT} = +6.5 dBm | 0 V 1.8 V 1.8 V | 0 V 0 V 1.8 V |
| ACLR E-UTRA at ± 10 MHz offset | - - - | -39 -39 -40 | -35 -35 -35 | dBc | P _{OUT} = +27.7 dBm P _{OUT} = +16 dBm P _{OUT} = +6.5 dBm | 0 V 1.8 V 1.8 V | 0 V 0 V 1.8 V |
| ACLR UTRA at ± 7.5 MHz offset | - - - | -39 -40 -40 | -37 -37 -37 | dBc | P _{OUT} = +27.7 dBm P _{OUT} = +16 dBm P _{OUT} = +6.5 dBm | 0 V 1.8 V 1.8 V | 0 V 0 V 1.8 V |
| ACLR UTRA at ± 12.5 MHz offset | - - - | -59 -60 -60 | -40 -40 -40 | dBc | P _{OUT} = +27.7 dBm P _{OUT} = +16 dBm P _{OUT} = +6.5 dBm | 0 V 1.8 V 1.8 V | 0 V 0 V 1.8 V |
| Power-Added Efficiency | 31 18 12 | 35 22 17 | - - - | % | P _{OUT} = +27.7 dBm P _{OUT} = +16 dBm P _{OUT} = +6.5 dBm | 0 V 1.8 V 1.8 V | 0 V 0 V 1.8 V |
| Quiescent Current (I _q) Low Bias Mode | - | 2.8 | 4.5 | mA | through V _{CC} pin | 1.8 V | 1.8 V |
| Mode Control Current | - | 0.06 | 0.15 | mA | through V _{MODE} pins, V _{MODE1,2} = +1.8 V | | |
| Enable Current | - | 0.03 | 0.1 | mA | through V _{EN} pin, V _{EN} = +1.8 V | | |
| BATT Current | - | 0.8 | 1.5 | mA | through V _{BATT} pin, V _{MODE1,2} = +1.8 V | | |
| Leakage Current | - | <5 | 10 | μA | V _{BATT} = V _{CC} = +4.35 V, V _{EN} = 0 V, V _{MODE1,2} = 0 V | | |
| Noise in Receive Band | - | -133 | - | dBm/Hz | 925 MHz to 960 MHz | | |
| Harmonics 2fo 3fo, 4fo | - - - | -50 -58 | -35 -45 | dBc | P _{OUT} ≤ +27.7 dBm | | |
| Input Impedance | - | - | 2:1 | VSWR | | | |
| Coupling Factor | - | 20 | - | dB | | | |
| Directivity | - | 20 | - | dB | | | |
| Coupler IN_OUT Daisy Chain Insertion Loss | - | 0.35 | - | dB | 698 MHz to 2620 MHz Pin 6-8, Shutdown Mode | | |
| Spurious Output Level (all spurious outputs) | - | - | -70 | dBc | P _{OUT} ≤ +27.7 dBm In-band load VSWR < 5:1 Out-of-band load VSWR < 10:1 Applies over all operating conditions | | |
| Load mismatch stress with no permanent degradation or failure | 8:1 | - | - | VSWR | Applies over full operating range | | |

Notes:

(1) ACLR and Efficiency measured at 897.5 MHz.

Table 5: Electrical Specifications - WCDMA Operation (R99 Modulation)
(T_C = +25 °C, V_{CC} = +3.4 V, V_{BATT} = +3.4 V, V_{EN} = +1.8 V, 50 Ω system)

| PARAMETER | MIN | TYP | MAX | UNIT | COMMENTS | | |
|---|--------------------------|----------------------------|-----------------------|------|--|---|-------------------------------------|
| | | | | | P _{OUT} | V _{MODE1} | V _{MODE2} |
| Gain | 25 14 9 | 27.5 17.5 12.5 | 31 21 16 | dB | P _{OUT} = +28.8 dBm P _{OUT} = +17 dBm P _{OUT} = +7.5 dBm | 0 V 1.8 V 1.8 V | 0 V 0 V 1.8 V |
| ACLR1 at 5 MHz offset ⁽¹⁾ | - - - | -41 -42 -41 | -37 -37 -37 | dBc | P _{OUT} = +28.8 dBm P _{OUT} = +17 dBm P _{OUT} = +7.5 dBm | 0 V 1.8 V 1.8 V | 0 V 0 V 1.8 V |
| ACLR2 at 10 MHz offset | - - - | -55 -57 -59 | -48 -48 -48 | dBc | P _{OUT} = +28.8 dBm P _{OUT} = +17 dBm P _{OUT} = +7.5 dBm | 0 V 1.8 V 1.8 V | 0 V 0 V 1.8 V |
| Power-Added Efficiency ⁽¹⁾ | 36 22 - 13 - | 40 26 17 18 10 | - - - - - | % | P _{OUT} = +28.8 dBm P _{OUT} = +17 dBm P _{OUT} = +13.5 dBm P _{OUT} = +7.5 dBm P _{OUT} = +3.5 dBm | 0 V 1.8 V 1.8 V 1.8 V 1.8 V | 0 V 0 V 0 V 1.8 V 1.8 V |
| Spurious Output Level (all spurious outputs) | - | - | <-70 | dBc | P _{OUT} ≤ +28.8 dBm In-band land VSWR < 5:1 Out-of-band load VSWR < 10 : 1 Applies over all operating ranges | | |
| Load mismatch stress with no permanent degradation or failure | 8:1 | - | - | VSWR | Applies over full operating range | | |

Notes:

(1) ACLR and Efficiency measured at 897.5 MHz.

PERFORMANCE DATA PLOTS:
(WCDMA Operation at 897.5 MHz and 50 Ω system)

Figure 4: WCDMA Gain (dB) over Temperature
($V_{BATT} = V_{CC} = +3.4\text{ V}$)

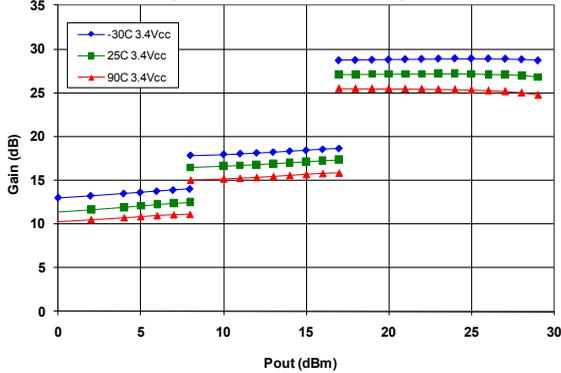


Figure 5: WCDMA Gain (dB) over Voltage
($T_c = 25\text{ °C}$)

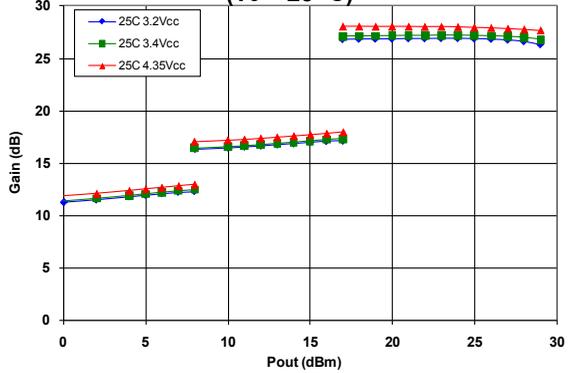


Figure 6: WCDMA PAE (%) over Temperature
($V_{BATT} = V_{CC} = +3.4\text{ V}$)

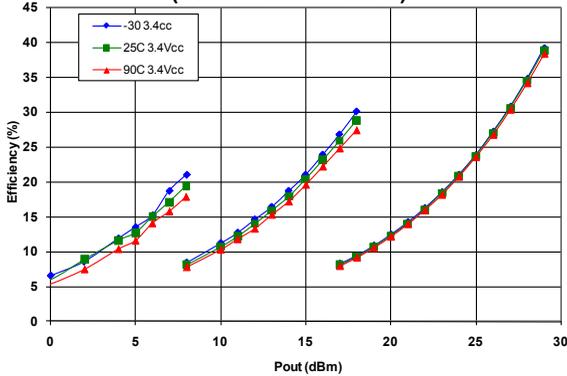


Figure 7: WCDMA PAE (%) over Voltage
($T_c = 25\text{ °C}$)

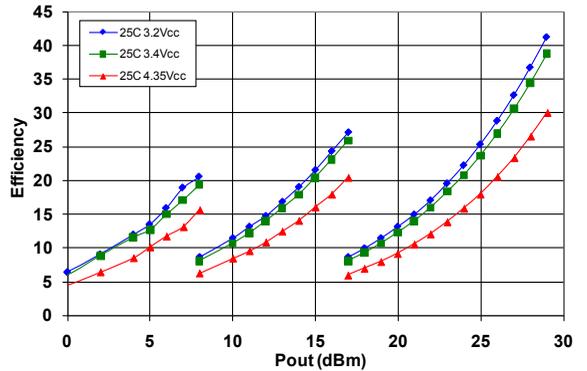


Figure 8: WCDMA ACLR1 (dBc) over Temperature
($V_{BATT} = V_{CC} = +3.4\text{ V}$)

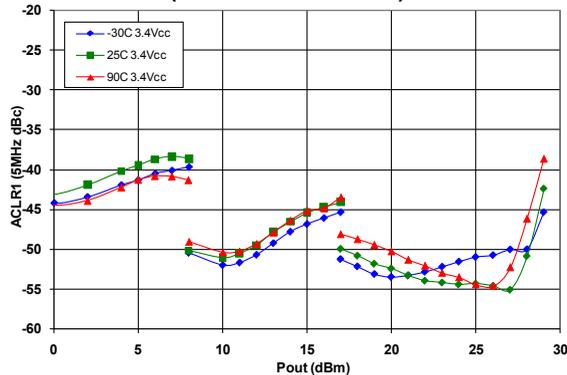
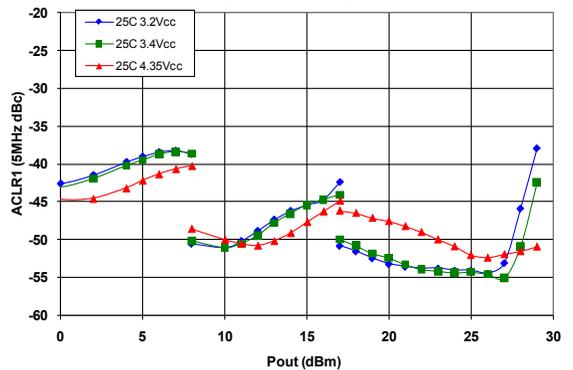


Figure 9: WCDMA ACLR1 (dBc) over Voltage
($T_c = 25\text{ °C}$)



APPLICATION INFORMATION

To ensure proper performance, refer to all related Application Notes on the ANADIGICS web site: <http://www.anadigics.com>

Shutdown Mode

The power amplifier may be placed in a shutdown mode by applying logic low levels (see Operating Ranges table) to the V_{EN} , V_{MODE1} and V_{MODE2} voltages.

Bias Modes

The power amplifier may be placed in either Low, Medium or High Bias modes by applying the appropriate logic level (see Operating Ranges table)

to the V_{MODE} voltages. The Bias Control table below lists the recommended modes of operation for various applications.

Three operating modes are recommended to optimize current consumption. High Bias/High Power operating mode is for P_{OUT} levels ≥ 16 dBm. At ~ 17 dBm - 6.5 dBm, the PA should be "Mode Switched" to Medium Power Mode. For P_{OUT} levels $\leq \sim 7.5$ dBm, the PA can be switched to Low Power Mode for even lower quiescent current consumption.

Table 6: Bias Control

| APPLICATION | P_{OUT} LEVELS | BIAS MODE | V_{EN} | V_{MODE1} | V_{MODE2} | V_{CC} | V_{BATT} |
|------------------------------|--------------------------------|-----------|----------|-------------|-------------|--------------|------------|
| Low power (Low Bias Mode) | $\leq +7.5$ dBm | Low | +1.8 V | +1.8 V | +1.8 V | 3.1 - 4.35 V | > 3.1 V |
| Med power (Medium Bias Mode) | $> +6.5$ dBm $\leq +17$ dBm | Low | +1.8 V | +1.8 V | 0 V | 3.1 - 4.35 V | > 3.1 V |
| High power (High Bias Mode) | $> +16$ dBm | High | +1.8 V | 0 V | 0 V | 3.1 - 4.35 V | > 3.1 V |
| Shutdown | - | Shutdown | 0 V | 0 V | 0 V | 3.1 - 4.35 V | > 3.1 V |

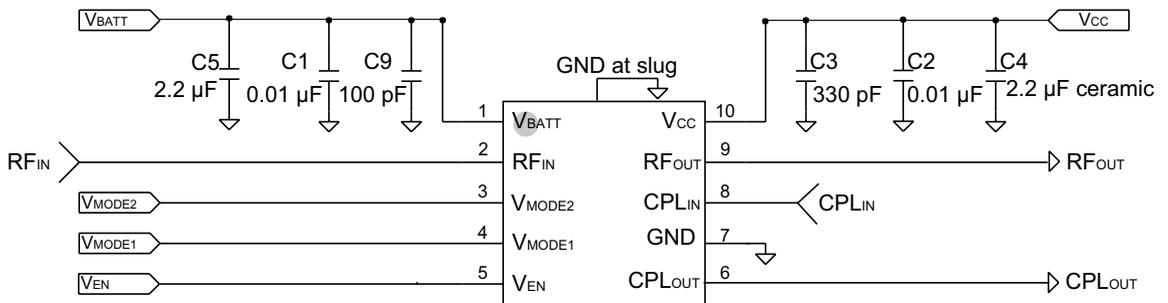
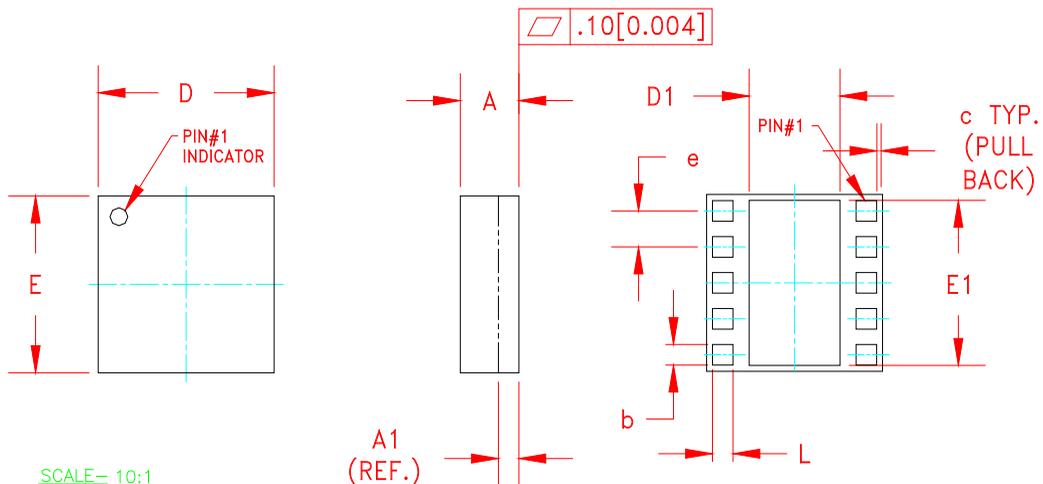


Figure 10: Evaluation Board Schematic

PACKAGE OUTLINE



| SYMBOL | MILLIMETERS | | | INCHES | | | NOTE |
|--------|--|------|------|--------|-------|-------|------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | |
| A | 0.91 | 1.03 | 1.13 | 0.035 | 0.041 | 0.044 | — |
| A1 | PLEASE REFER TO LAMINATE CONTROL DRAWING | | | | | | — |
| b | 0.32 | 0.35 | 0.40 | 0.013 | 0.014 | 0.016 | 3 |
| c | — | 0.10 | — | — | 0.004 | — | — |
| D | 2.88 | 3.00 | 3.12 | 0.113 | 0.118 | 0.123 | — |
| D1 | 1.45 | 1.50 | 1.57 | 0.057 | 0.059 | 0.062 | 3 |
| E | 2.88 | 3.00 | 3.12 | 0.113 | 0.118 | 0.123 | — |
| E1 | 2.70 | 2.75 | 2.85 | 0.106 | 0.108 | 0.112 | 3 |
| e | 0.60 | | | 0.024 | | | 3 |
| L | 0.32 | 0.35 | 0.40 | 0.013 | 0.014 | 0.016 | 3 |

NOTES:

1. CONTROLLING DIMENSIONS: MILLIMETERS
2. UNLESS SPECIFIED TOLERANCE=±0.076[0.003].
3. PADS (INCLUDING CENTER) SHOWN UNIFORM SIZE FOR REFERENCE ONLY. ACTUAL PAD SIZE AND LOCATION WILL VARY WITHIN MIN. AND MAX. DIMENSIONS ACCORDING TO SPECIFIC LAMINATE DESIGN.
4. UNLESS SPECIFIED DIMENSIONS ARE SYMMETRICAL ABOUT CENTER LINES SHOWN.
5. LAMINATE CONTROL DRAWING SPECIFIED BY PART NUMBER.

Figure 11: M45 Package Outline - 10 Pin 3 mm x 3 mm x 1 mm Surface Mount Module

TOP BRAND

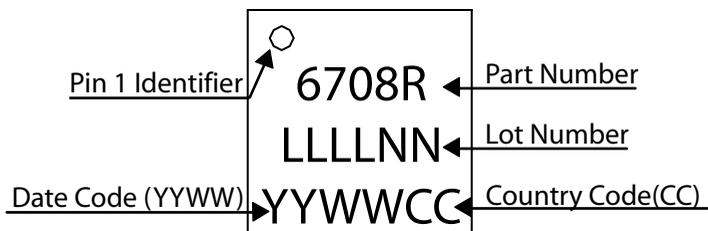
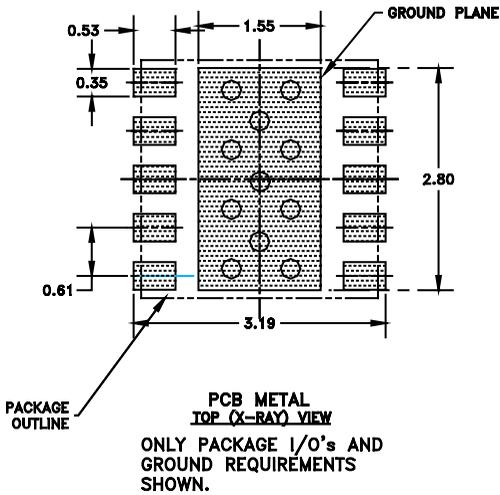


Figure 12: Branding Specification - M45 Package

PCB AND STENCIL DESIGN GUIDELINE



NOTES:

- (1) OUTLINE DRAWING REFERENCE: P8002478_E
- (2) UNLESS SPECIFIED DIMENSIONS ARE SYMMETRICAL ABOUT CENTER LINES SHOWN.
- (3) DIMENSIONS IN MILLIMETERS.
- (4) VIAS SHOWN IN PCB METAL VIEW ARE FOR REFERENCE ONLY. NUMBER & SIZE OF THERMAL VIAS REQUIRED DEPENDENT ON HEAT DISSIPATION REQUIREMENT AND THE PCB PROCESS CAPABILITY.
- (5) RECOMMENDED STENCIL THICKNESS: APPROX. 0.150mm (6 Mils)

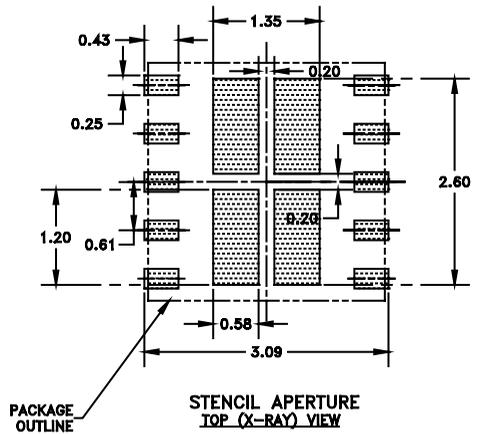
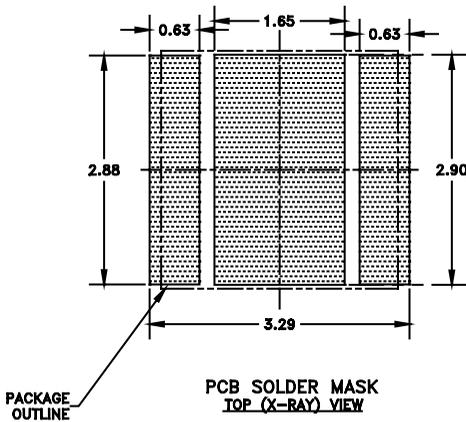
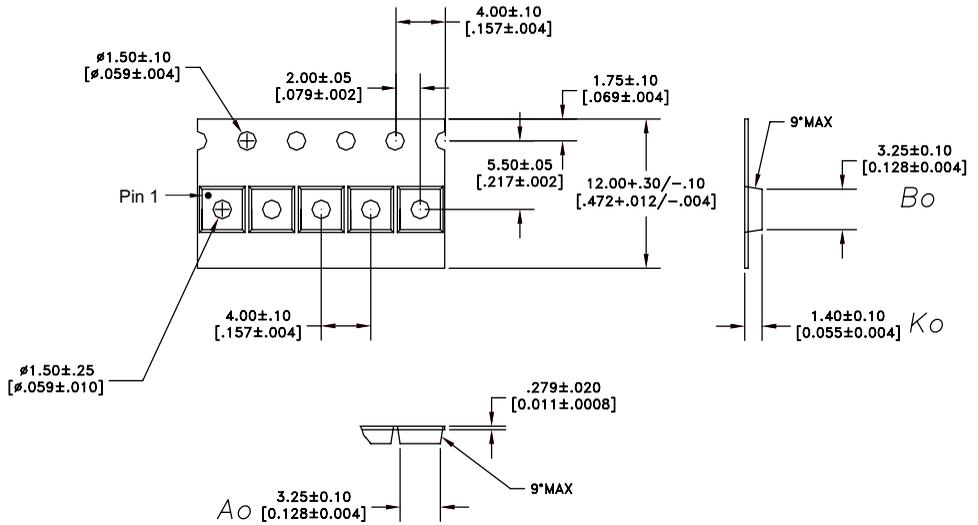


Figure 13: Recommended PCB Layout Information

COMPONENT PACKAGING



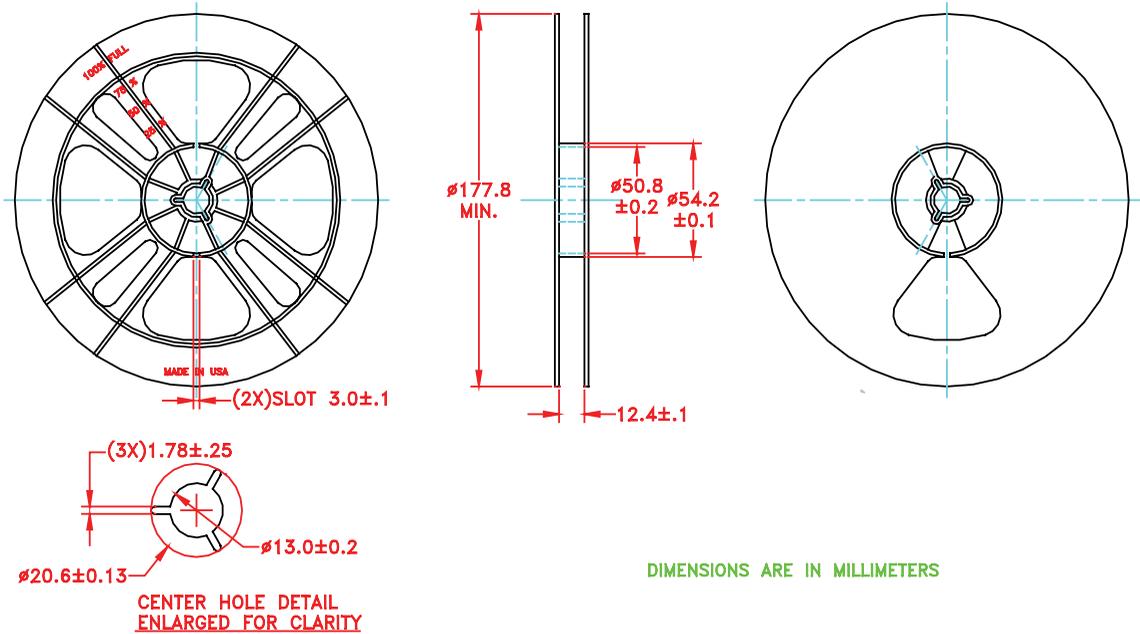
NOTES:

- 1. MATERIAL: 3000 (CARBON FILLED POLYCARBONATE)
100% RECYCLABLE.

DIMENSIONS ARE IN MILLIMETERS [INCHES]

DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994

Figure 14: Carrier Tape



DIMENSIONS ARE IN MILLIMETERS

NOTES:

- 1. MATERIAL: BLACK CARBON POLYSTYRENE
- SURFACE RESISTIVITY: 1×10^4 TO 1×10^9 ohms/square

DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994

Figure 15: Reel

ORDERING INFORMATION

| ORDER NUMBER | TEMPERATURE RANGE | PACKAGE DESCRIPTION | COMPONENT PACKAGING |
|---------------|-------------------|---|-------------------------------------|
| ALT6708RM45Q7 | -40 °C to +90 °C | RoHS Compliant 10 Pin 3 mm x 3 mm x 1 mm Surface Mount Module | Tape and Reel, 2500 pieces per Reel |
| ALT6708RM45P9 | -40 °C to +90 °C | RoHS Compliant 10 Pin 3 mm x 3 mm x 1 mm Surface Mount Module | Partial Tape and Reel |



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